

In the Claims:

No amendments to the claims are presented.

Claims 1-3 (Cancelled)

4. (Previously Presented) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen as a carrier gas,

wherein the epitaxial layer comprises a SiGe epitaxial layer, and

wherein the method is carried out at a temperature between 500°C and 600°C.

5. (Previously Presented) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen as a carrier gas,

wherein the epitaxial layer comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.

6. (Cancelled)

7. (Previously Presented) The method as claimed in claim 5, which is carried out at a temperature that facilitates a CVD growth rate of an epitaxial layer that is substantially greater than a CVD growth rate of such an epitaxial layer using hydrogen as a carrier gas.

Claims 8-17 (Cancelled)

18. (Previously Presented) A method as claimed in claim 4, wherein the source gases include SiH_4 and GeH_4 .

19. (Previously Presented) A method as claimed in claim 5, which is carried out at a temperature of less than about 600°C.

20. (Cancelled)

21. (Previously Presented) A method as claimed in claim 5, which is carried out at a temperature between 500°C and 600°C.

22. (Previously Presented) A method as claimed in claim 5, wherein the source gases include SiH₄, GeH₄ and SiH₃CH₃.